



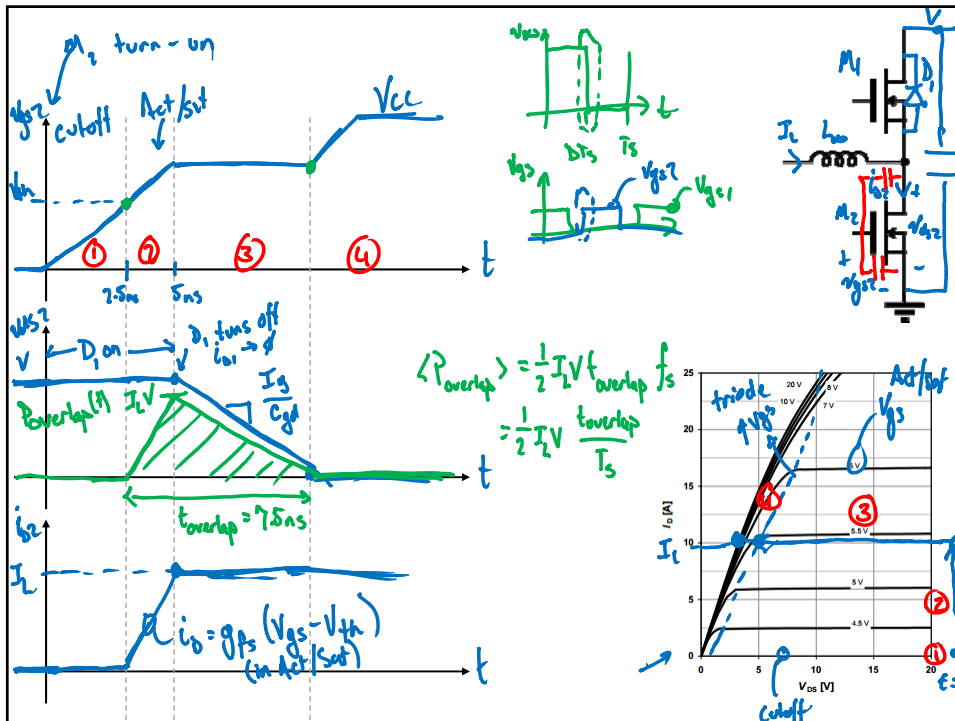
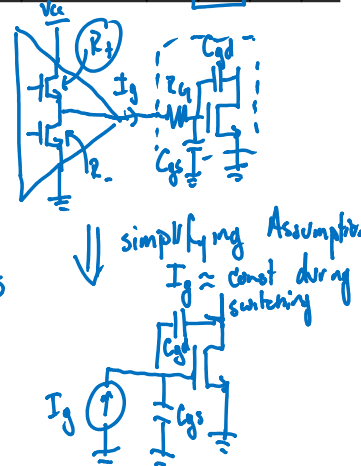
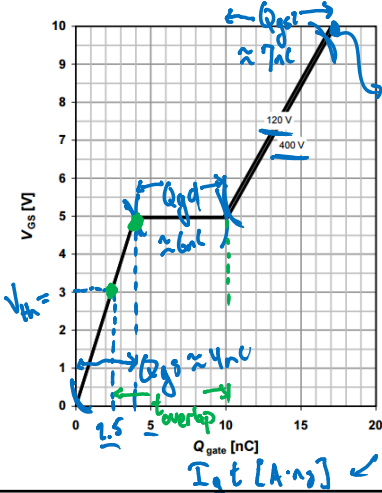
Overlap Time

9 Typ. gate charge

$V_{GS} = f(Q_{gate}); I_D = 5.2 \text{ A pulsed}$

parameter: V_{DD}

Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 0.34 \text{ mA}$	2.5	3	3.5
Gate resistance	R_G	$f = 1 \text{ MHz, open drain}$	-	1.8	-
				Ω	





Device Transconductance

